

### N-Channel Super Junction Power MOSFET III

### **General Description**

The series of devices use advanced trench gate super junction technology and design to provide excellent RDS(ON) with low gate charge. This super junction MOSFET fits the industry's AC-DC SMPS requirements for PFC, AC/DC power conversion, and industrial power applications.

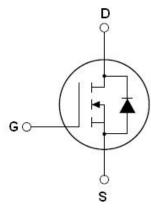
#### **Features**

- Optimized body diode reverse recovery performance
- ●Low on-resistance and low conduction losses
- Small package
- ●Ultra Low Gate Charge cause lower driving requirements
- ●100% Avalanche Tested
- ROHS compliant

### **Application**

- Power factor correction (PFC)
- Switched mode power supplies(SMPS)
- Uninterruptible Power Supply (UPS)
- LLC Half-bridge

V <sub>DS</sub>	650	V
R <sub>DS(ON)TYP</sub>	120	mΩ
I <sub>D</sub>	28	A



Schematic diagram

♦ Intrinsic fast-recovery body diode

### **Package Marking And Ordering Information**

Device	Device Package	Marking
NCE65TF130D	TO-263	NCE65TF130D
NCE65TF130	TO-220	NCE65TF130
NCE65TF130F	TO-220F	NCE65TF130F







TO-263

TO-220F

Table 1. Absolute Maximum Ratings (T <sub>c</sub> =25 <sup>°</sup> C)						
Parameter	Symbol	NCE65TF130D NCE65TF130	NCE65TF130F	Unit		
Drain-Source Voltage (Vcs=0V)	V <sub>DS</sub>	65	50	V		
Gate-Source Voltage (V <sub>DS=0</sub> V) AC (f>1 Hz)	Vgs	±	40	V		
Gate-Source Voltage (V <sub>DS</sub> =0V)	Vgs	±30		V		
Continuous Drain Current at Tc=25°C	I <sub>D (DC)</sub>	28	28*	А		
Continuous Drain Current at Tc=100°C	I <sub>D (DC)</sub>	18	18*	А		
Pulsed drain current (Note 1)	I <sub>DM (pluse)</sub>	112 112*		Α		
Maximum Power Dissipation(Tc=25℃)	P <sub>D</sub>	260 35		W		
Derate above 25°C		2.08	0.28	W/°C		
Single pulse avalanche energy (Note 2)	Eas	676		mJ		
Avalanche current <sup>(Note 1)</sup>	I <sub>AR</sub>	5.2		Α		
Repetitive Avalanche energy , $t_{\text{AR}}$ limited by $T_{\text{jmax}}$ (Note 1)	E <sub>AR</sub>	3.2		mJ		



Parameter	Symbol	NCE65TF130D NCE65TF130	NCE65TF130F	Unit
Drain Source voltage slope, V <sub>DS</sub> ≤480 V,	dv/dt	50		V/ns
Reverse diode dv/dt, V <sub>DS</sub> ≤480 V,I <sub>SD</sub> <i<sub>D</i<sub>	dv/dt	5	0	V/ns
Operating Junction and Storage Temperature Range	$T_{J}, T_{STG}$	-55	+150	°C

<sup>\*</sup> limited by maximum junction temperature

### **Table 2. Thermal Characteristic**

Parameter	Symbol	NCE65TF130D NCE65TF130	NCE65TF130F	Unit
Thermal Resistance, Junction-to-Case (Maximum)	R <sub>thJC</sub>	0.48	3.57	°C /W
Thermal Resistance, Junction-to-Ambient (Maximum)	R <sub>thJA</sub>	62	80	°C /W

 Table 3. Electrical Characteristics (TA=25<sup>o</sup>Cunless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit	
On/off states							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250µA	650			V	
Zero Gate Voltage Drain Current(Tc=25℃)	I <sub>DSS</sub>	V <sub>DS</sub> =650V,V <sub>GS</sub> =0V			3	μA	
Zero Gate Voltage Drain Current(Tc=125℃)	I <sub>DSS</sub>	V <sub>DS</sub> =650V,V <sub>GS</sub> =0V			100	μΑ	
Gate-Body Leakage Current	Igss	V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V			±100	nA	
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS},I_{D}=250\mu A$	2.6	3.5	4.3	V	
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =14A		120	149	mΩ	
Dynamic Characteristics					•		
Input Capacitance	C <sub>lss</sub>	V <sub>DS</sub> =50V,V <sub>GS</sub> =0V,		2070		pF	
Output Capacitance	Coss	F=1.0MHz		120		pF	
Effective output capacitance, energy related	C <sub>o(er)</sub>	V <sub>GS</sub> =0 V,V <sub>DS</sub> =0480 V		60		pF	
Effective output capacitance, time related	C <sub>o(tr)</sub>	ID=constant, V <sub>GS</sub> =0 V V <sub>DS</sub> =0480V		311		pF	
Total Gate Charge	Qg	\/ 400\/ L 00A		37.5		nC	
Gate-Source Charge	Qgs	V <sub>DS</sub> =480V,I <sub>D</sub> =28A,		13		nC	
Gate-Drain Charge	Q <sub>gd</sub>	V <sub>GS</sub> =10V		11.5		nC	
Switching times			•				
Turn-on Delay Time	t <sub>d(on)</sub>			14		nS	
Turn-on Rise Time	t <sub>r</sub>	$V_{DD}$ =380 $V$ , $I_{D}$ =14 $A$ ,		12		nS	
Turn-Off Delay Time	t <sub>d(off)</sub>	$R_G$ =2.3 $\Omega$ , $V_{GS}$ =10 $V$		65		nS	
Turn-Off Fall Time	t <sub>f</sub>			11		nS	
Source- Drain Diode Characteristics							
Source-drain current(Body Diode)	I <sub>SD</sub>	T. 0500			28	Α	
Pulsed Source-drain current(Body Diode)	I <sub>SDM</sub>	T <sub>C</sub> =25°C			112	Α	
Forward On Voltage	V <sub>SD</sub>	Tj=25°C,I <sub>SD</sub> =28A,V <sub>GS</sub> =0V		0.9	1.2	V	
Reverse Recovery Time	t <sub>rr</sub>			190		nS	
Reverse Recovery Charge	Qrr			2		uC	
Peak Reverse Recovery Current	I <sub>rrm</sub>			21		Α	

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature

<sup>2.</sup> Tj=25  $^{\circ}\text{C}$  ,VDD=50V,VG=10V, RG=25 $\Omega$ 



### TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS (curves)

Figure 1. Safe operating area

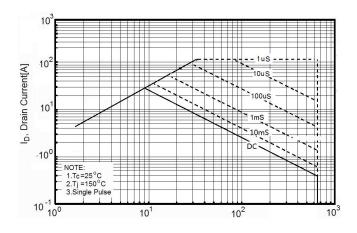


Figure 3. Source-Drain Diode Forward Voltage

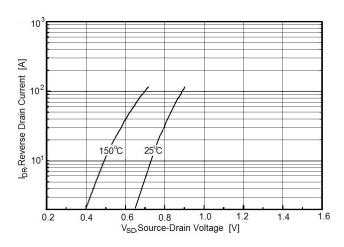


Figure 5. Transfer characteristics

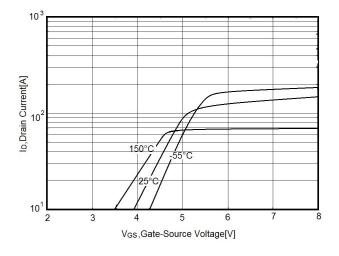


Figure 2. Safe operating area for TO-220F

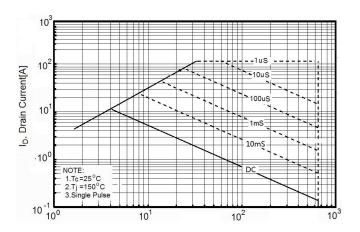


Figure 4. Output characteristics

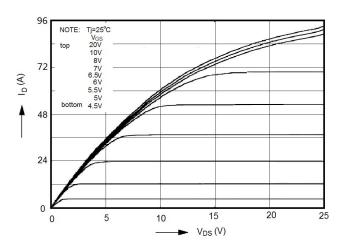


Figure 6. Static drain-source on resistance

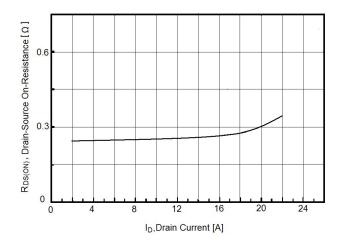




Figure 7. R<sub>DS(ON)</sub> vs Junction Temperature

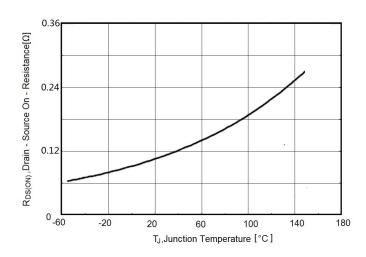


Figure 8. BV<sub>DSS</sub> vs Junction Temperature

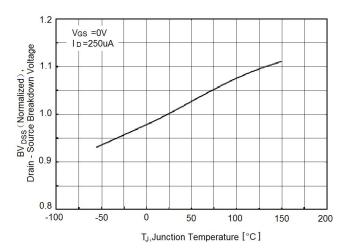


Figure 9. Maximum ID vs Junction Temperature

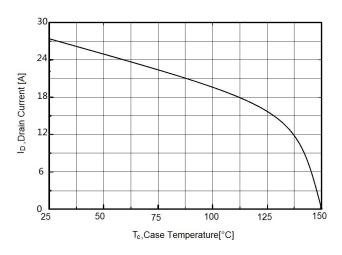


Figure 10. Gate charge waveforms

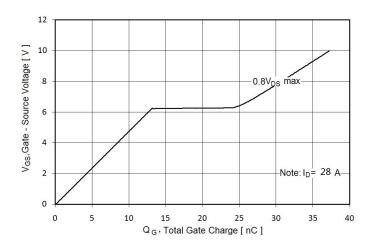


Figure 11. Capacitance

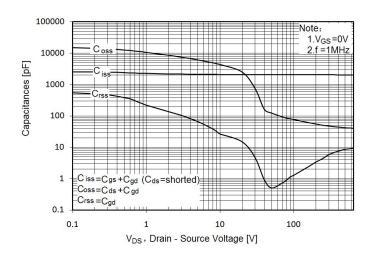


Figure 12. Transient Thermal Impedance

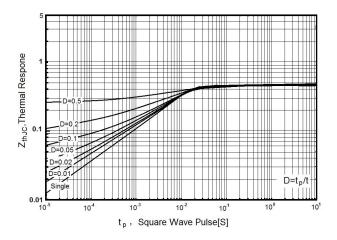
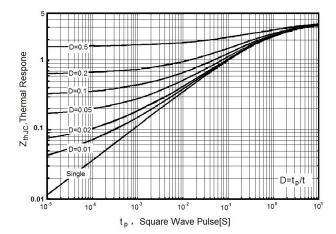




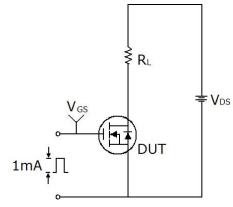
Figure 13. Transient Thermal Impedance for TO-220F

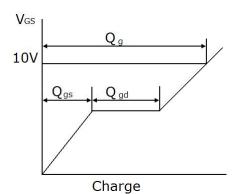




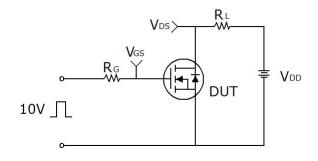
### **Test circuit**

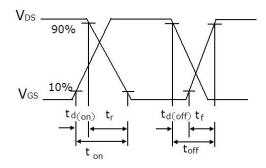
### 1) Gate charge test circuit & Waveform



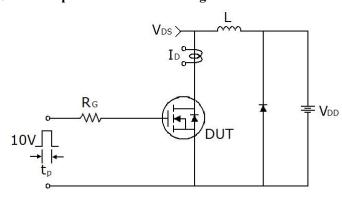


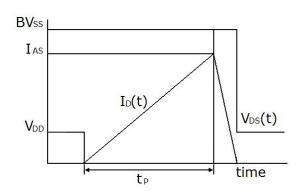
### 2) Switch Time Test Circuit:





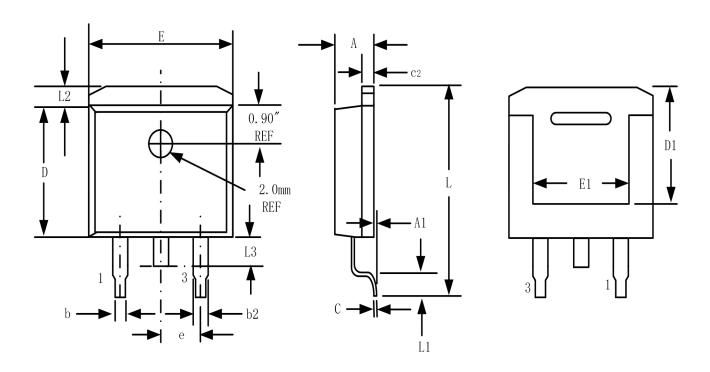
### 3) Unclamped Inductive Switching Test Circuit & Waveforms







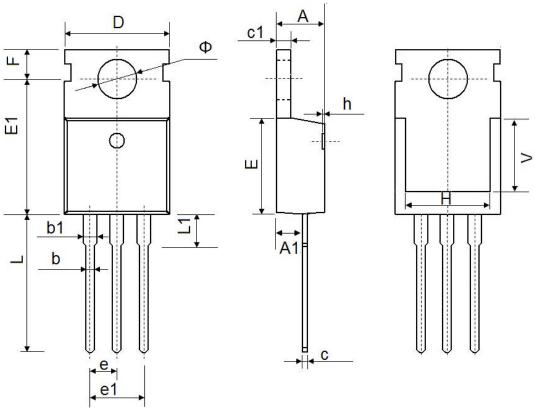
# **TO-263-3L Package Information**



Symbol	Dimensions	In Millimeters	Dimension	s In Inches
Symbol	Min.	Max.	Min.	Max.
А	4.32	4.57	0.170	0.180
A1	-	0.25		0.010
b	0.71	0.94	0.028	0.037
b2	1.15	1.40	0.045	0.055
С	0.46	0.61	0.018	0.024
c2	1.22	1.40	0.048	0.055
D	8.89	9.40	0.350	0.370
D1	8.01	8.23	0.315	0.324
E	10.04	10.28	0.395	0.405
E1	7.88	8.08	0.310	0.318
е	2.54	BSC	0.100	) BSC
L	14.73	15.75	0.580	0.620
L1	2.29	2.79	0.090	0.110
L2	1.15	1.39	0.045	0.055
L3	1.27	1.77	0.050	0.070



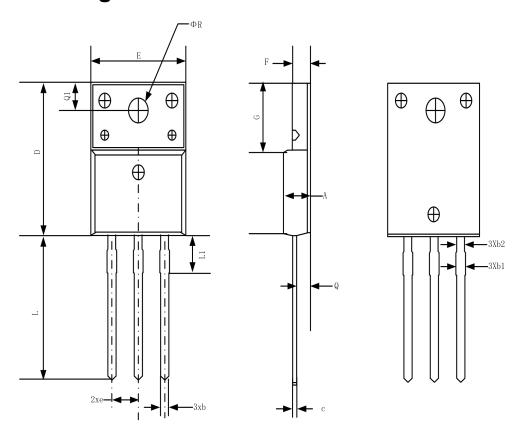
# **TO-220-3L-C Package Information**



Cumbal	Dimensions	In Millimeters	Dimensions In Inches	
Symbol	Min.	Max.	Min.	Max.
А	4.400	4.600	0.173	0.181
A1	2.250	2.550	0.089	0.100
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
С	0.330	0.650	0.013	0.026
c1	1.200	1.400	0.047	0.055
D	9.910	10.250	0.390	0.404
E	8.9500	9.750	0.352	0.384
E1	12.650	12.950	0.498	0.510
е	2.540 TYP.		0.100	TYP.
e1	4.980	5.180	0.196	0.204
F	2.650	2.950	0.104	0.116
Н	7.900	8.100	0.311	0.319
h	0.000	0.300	0.000	0.012
L	12.900	13.400	0.508	0.528
L1	2.850	3.250	0.112	0.128
V	7.50	0 REF.	0.295	REF.
Ф	3.400	3.800	0.134	0.150



# **TO-220F Package Information**



Symbol	Dimensions	Dimensions In Millimeters		s In Inches
Symbol	Min.	Max.	Min.	Max.
А	4.50	4.83	0.18	0. 19
b	0.70	0.91	0.03	0.04
b1	1.20	1.47	0.05	0.06
b2	1.10	1.38	0.04	0.05
С	0.45	0.63	0.02	0.02
D	15.67	16.07	0.62	0.63
е	2.54	BSC	0.10	BSC
E	9.96	10.36	0.39	0.41
F	2.34	2.74	0.09	0.11
G	6.48	6.90	0. 26	0. 27
L	12.68	13.30	0.50	0. 52
L1	3.13	3.50	0.12	0.14
Q	2.56	2.93	0.10	0.12
Q1	3.20	3.40	0.13	0.13
ФК	3.08	3.28	0.12	0.13



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